华润微电子(重庆)有限公司

CRSG026N10NZ

SkyMOS1 N-MOSFET 100V, 2.2mΩ, 230A

Features

- Uses CRM(CQ) advanced SkyMOS1 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

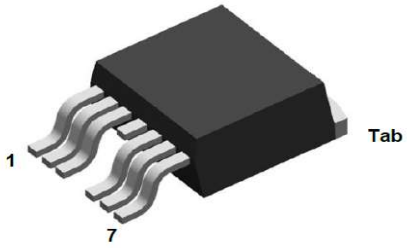
V_{DS}	100V
$R_{DS(on)}$	2.2mΩ
I_D	230A

100% DVDS Tested

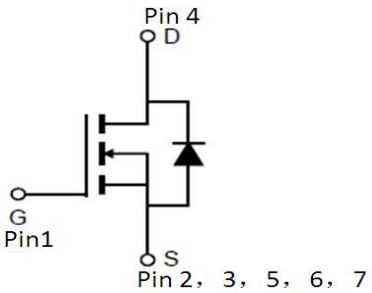
100% Avalanche Tested

Applications

- Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)



CRSG026N10NZ



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSG026N10NZ	CRSG026N10NZ	TO-263-6L	Tape	N/A	N/A	800pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	100	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 234 240 148	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	936	A
Avalanche energy, single pulse (L=0.5mH, Rg=25Ω)[1]	E_{AS}	529	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	260	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

Notes:1.EAS was tested at Tj = 25℃, ID = 46A.

Thermal Resistance

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Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	R_{thJC}	-	0.30	0.48	°C/W	
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	-	-	62	°C/W	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	100	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	- -	0.05 -	1 100	μA	V_{DS}=100V,V_{GS}=0V T_j=25°C T_j=125°C
Gate-source leakage current	I_{GSS}	-	±10	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	2.2	2.6	mΩ	V_{GS}=10V, I_D=90A
Transconductance	g_{fs}	-	197.2	-	S	V_{DS}=5V,I_D=100A
Dynamic Characteristic						
Input Capacitance	C_{iss}	7570	11355	17032.5	pF	V_{GS}=0V, V_{DS}=50V, f=1MHz
Output Capacitance	C_{oss}	964	1446	2169		
Reverse Transfer Capacitance	C_{rss}	36	54	81		
Gate Total Charge	Q_G	113	169	254	nC	V_{GS}=10V, V_{DS}=50V, I_D=100A, f=1MHz
Gate-Source charge	Q_{gs}	45	67	101		
Gate-Drain charge	Q_{gd}	20	30	45		
Turn-on delay time	$t_{d(on)}$	23	35	53	ns	V_{GS}=10V, V_{DD}=50V, R_{G_ext}=3.0Ω
Rise time	t_r	74	111	167		
Turn-off delay time	$t_{d(off)}$	56	84	126		
Fall time	t_f	75	112	168		
Gate resistance	R_G	-	2.0	-	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.9	1.4	V	V_{GS}=0V,I_{SD}=90A
Body Diode Reverse Recovery Time	t_{rr}	51	101	202	ns	I_F=100A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	169	338	676	nC	

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Typical Performance Characteristics

Fig 1: Output Characteristics

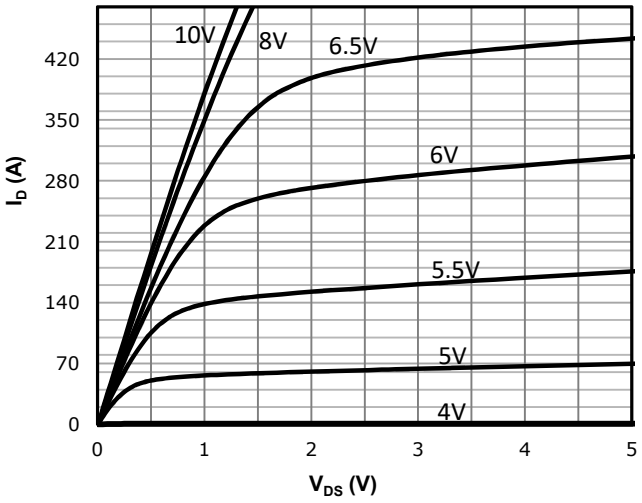
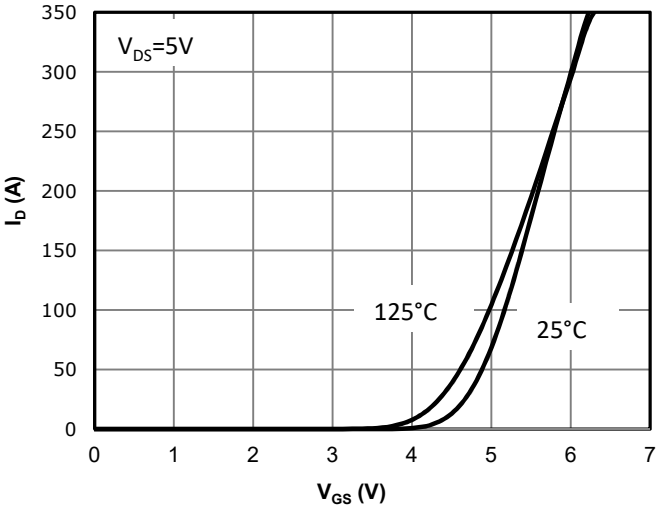


Fig 2: Transfer Characteristics



3: Rds(on) vs Drain Current and Gate Voltage

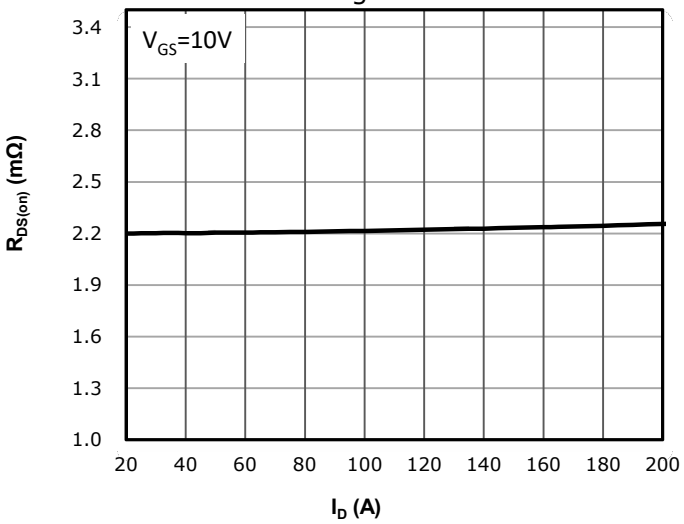


Fig 4: Rds(on) vs Gate Voltage

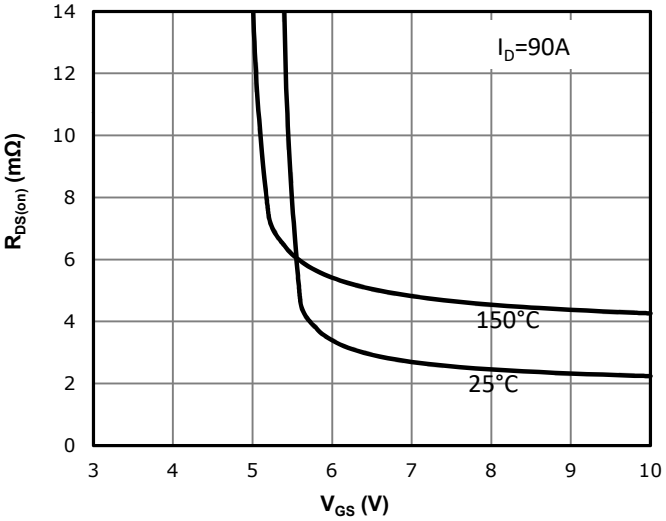


Fig 5: Rds(on) vs. Temperature

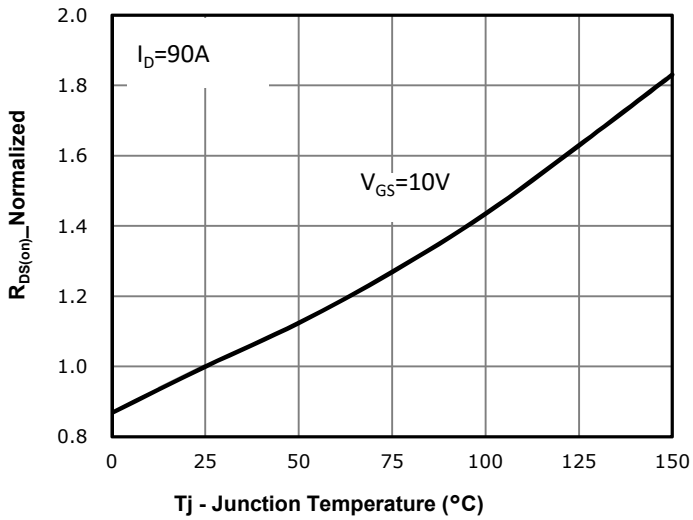
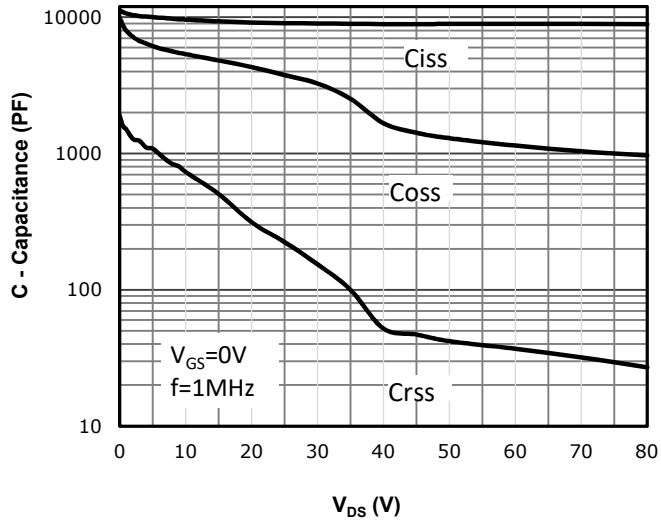


Fig 6: Capacitance Characteristics



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Fig 7: Gate Charge Characteristics

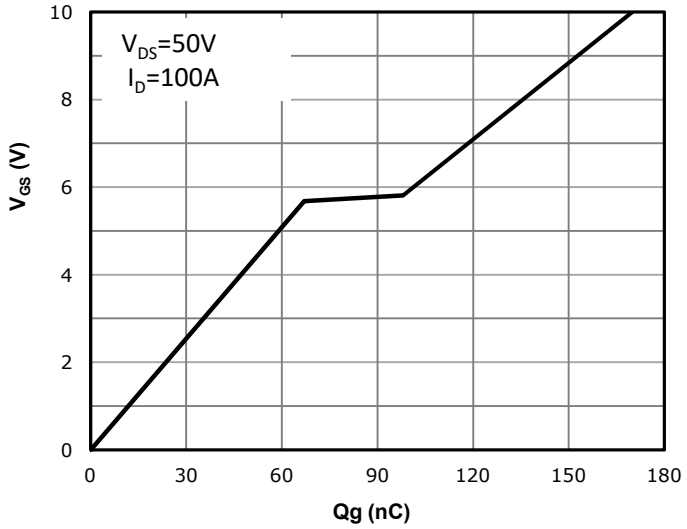


Fig 8: Body-diode Forward Characteristics

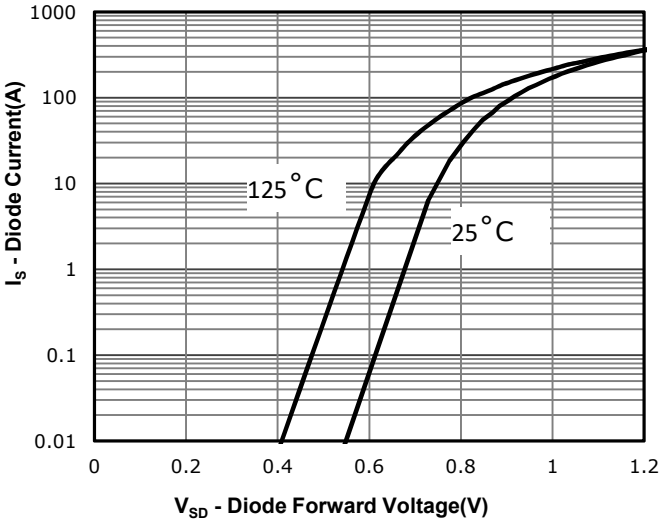


Fig 9: Power Dissipation

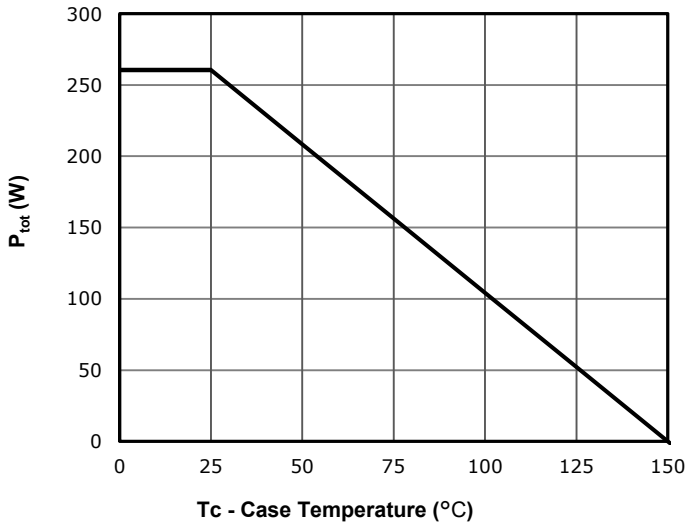


Fig 10: Drain Current Derating

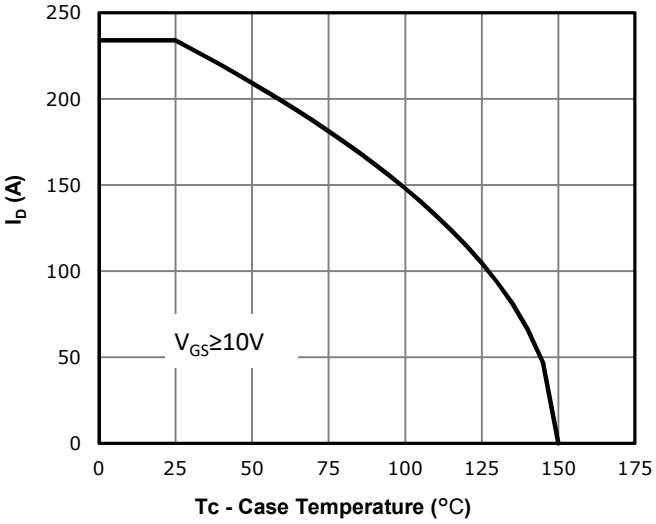
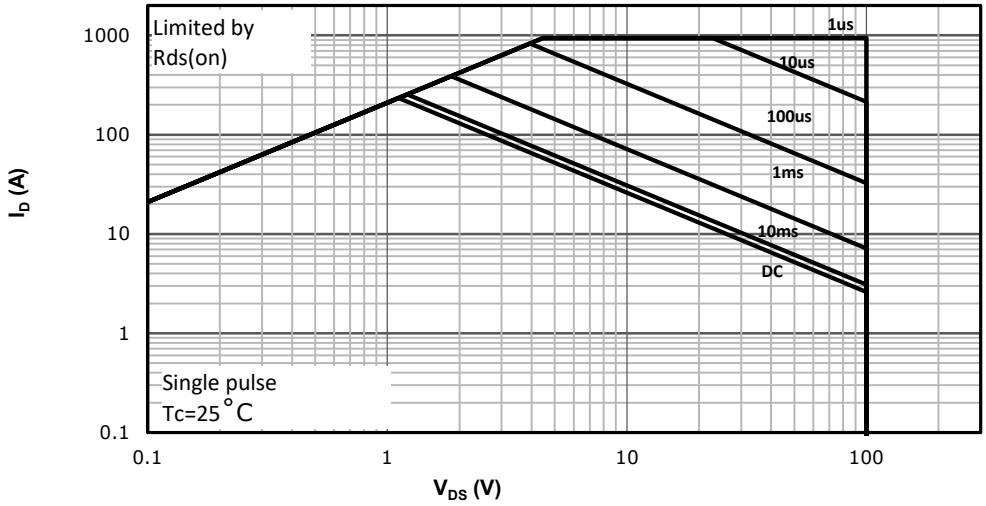
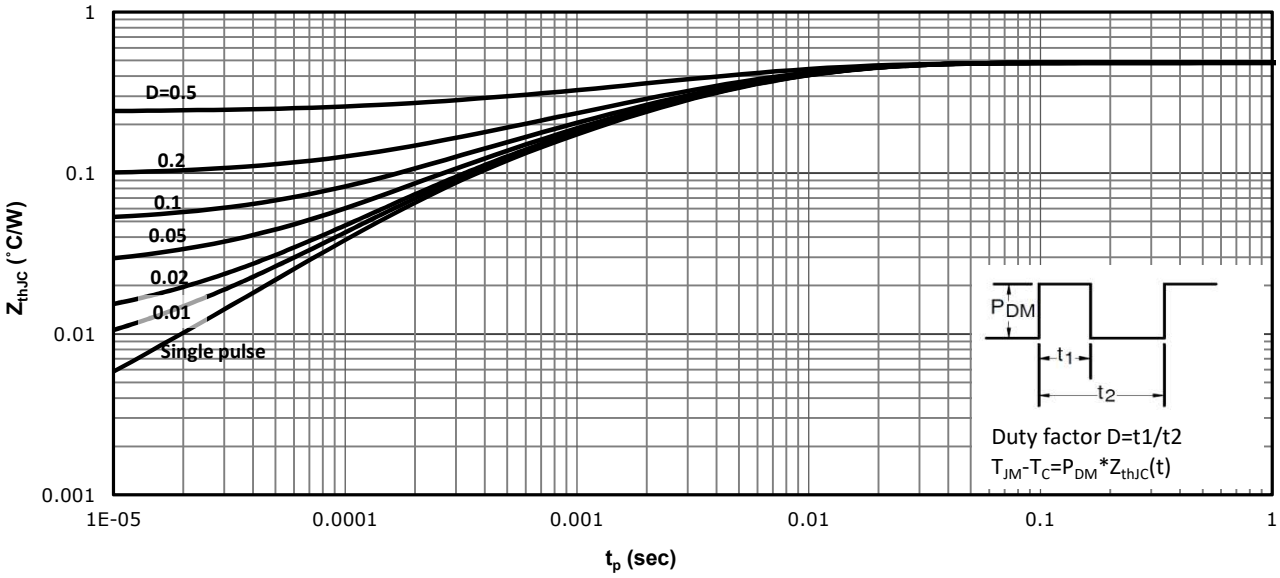


Fig 11: Safe Operating Area



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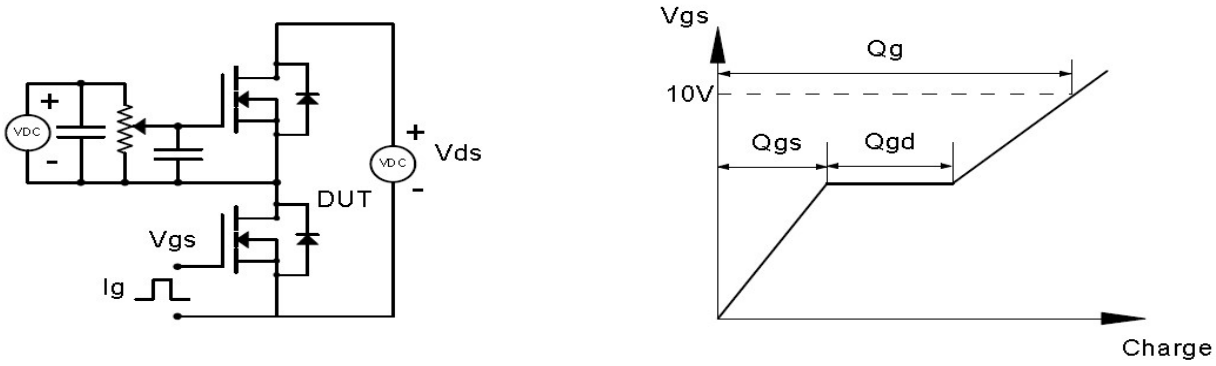
Fig 12: Max. Transient Thermal Impedance



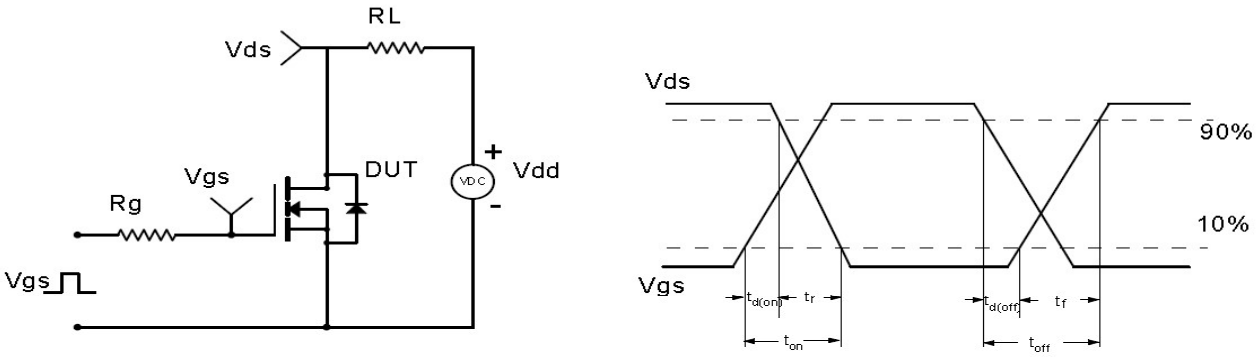
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Test Circuit & Waveform

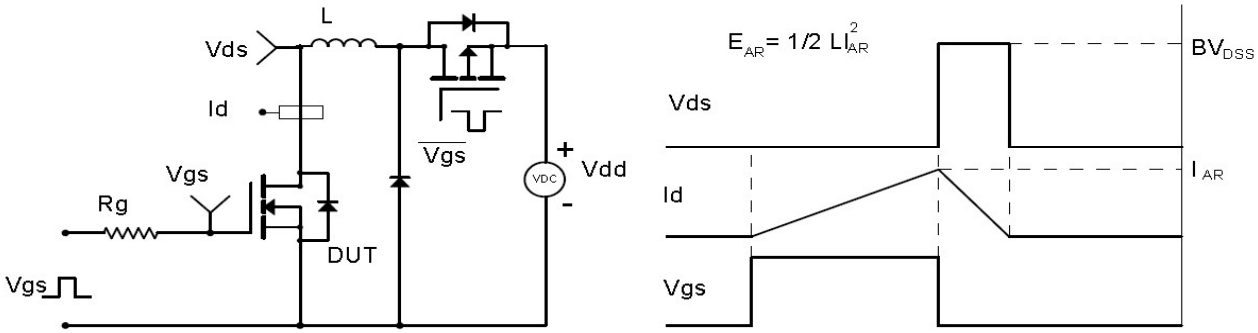
Gate Charge Test Circuit & Waveform



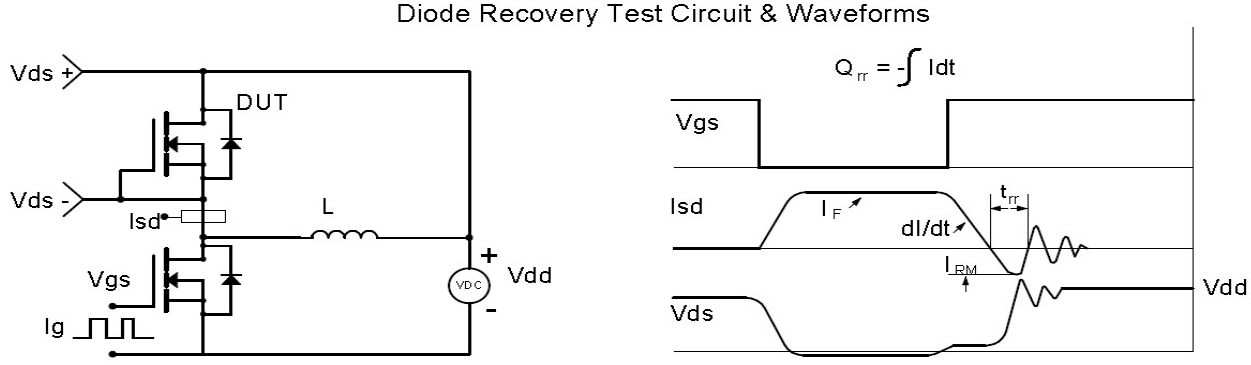
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

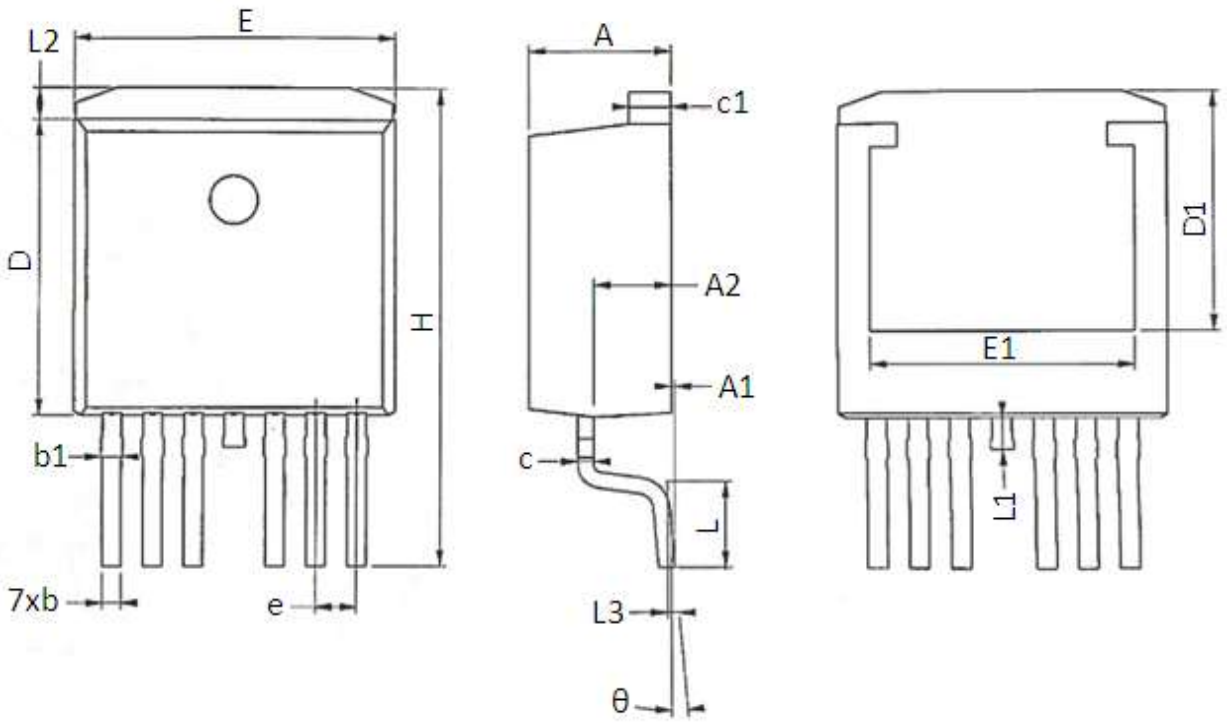


Diode Recovery Test Circuit & Waveforms



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Package Outline: TO-263-6L



Symbol		Dimensions In Millimeters		Dimensions In Inches	
		Min.	Max.	Min.	Max.
A		4.24	4.64	0.167	0.183
A1		0.00	0.25	0.000	0.010
A2		2.25	2.70	0.089	0.106
b		0.50	0.70	0.020	0.028
b1		0.50	0.90	0.020	0.035
c		0.40	0.60	0.016	0.024
c1		1.15	1.40	0.045	0.055
D		8.82	9.45	0.347	0.372
D1		6.80	--	0.268	--
e		1.27 BSC		0.050 BSC	
E		9.80	10.36	0.386	0.408
E1		7.25	--	0.285	--
H		14.61	15.88	0.575	0.625
L		1.78	3.00	0.070	0.118
L1		0.85	1.60	0.033	0.063
L2		0.80	1.60	0.031	0.063
L3		0.254 BSC		0.010 BSC	
θ	Option A	0°	8°	0°	8°
	Option B	0°	-8°	0°	-8°

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Revision History

Revison	Date	Major changes
1.0	2022/12/26	Release of formal version.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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